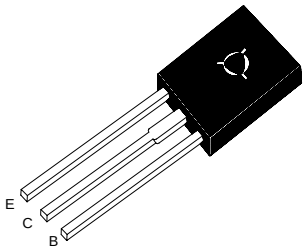
ST 2SD882HT

NPN Silicon Power Transistor

The transistor is subdivided into four groups, R, Q, P and E, according to its DC current gain.



TO-126 Plastic Package

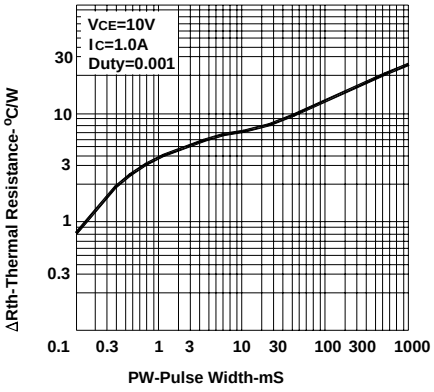
Absolute Maximum Ratings (T_a = 25℃)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	60	V
Collector Emitter Voltage	V_{CEO}	30	V
Emitter Base Voltage	V_{EBO}	5	V
Collector Current	I_C	3	A
Collector Current (Pulse)	I_{CP}	7	A
Total Power Dissipation(T_a = 25℃)	P_{tot}	1	W
Total Power Dissipation(T_C = 25℃)	P_{tot}	10	W
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	- 55 to + 150	℃

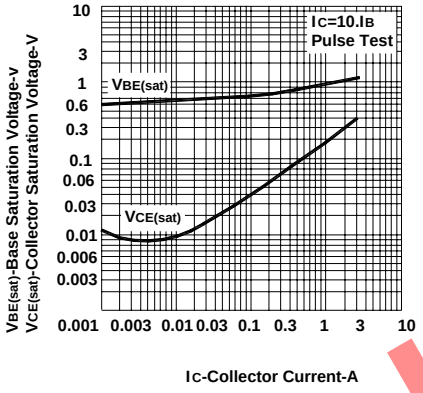
Characteristics at T_a = 25℃

Parameter		Symbol	Min.	Typ.	Max.	Unit
DC Current Gain						
at V_{CE} = 2 V, I_C = 1 A	Current Gain Group R	h_{FE}	60	-	120	-
	Q	h_{FE}	100	-	200	-
	P	h_{FE}	160	-	320	-
	E	h_{FE}	200	-	400	-
at V_{CE} = 2 V, I_C = 20 mA		h_{FE}	30	-	-	-
Collector Base Cutoff Current at V_{CB} = 60 V		I_{CBO}	-	-	1	μA
Emitter Base Cutoff Current at V_{EB} = 3 V		I_{EBO}	-	-	1	μA
Collector Emitter Saturation Voltage at I_C = 2 A, I_B = 0.2 A		$V_{CE(sat)}$	-	-	0.5	V
Base Emitter Saturation Voltage at I_C = 2 A, I_B = 0.2 A		$V_{BE(sat)}$	-	-	2	V
Gain Bandwidth Product at V_{CE} = 5 V, I_C = 0.1 A		f_T	-	90	-	MHz
Output Capacitance at V_{CB} = 10 V, f = 1 MHz		C_{ob}	-	45	-	pF

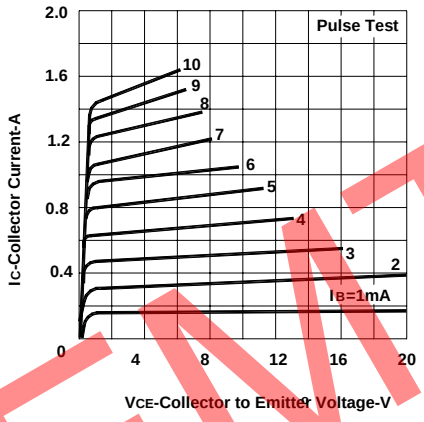
THERMAL RESISTANCE vs.
PULSE WIDTH



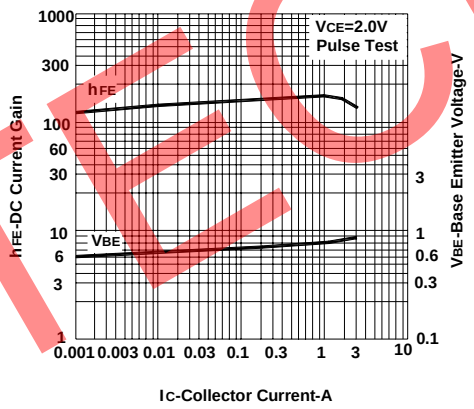
BASE AND COLLECTOR SATURATION
VOLTAGE vs. COLLECTOR CURRENT



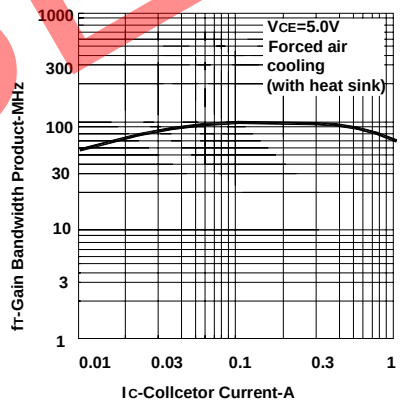
COLLECTOR CURRENT vs.
COLLECTOR TO EMITTER VOLTAGE



DC CURRENT GAIN, BASE TO EMITTER
VOLTAGE vs. COLLECTOR CURRENT



GAIN BANDWIDTH PRODUCT vs.
COLLCETOR CURRENT



INPUT AND OUTPUT CAPACITANCE vs.
REVERSE VOLTAGE